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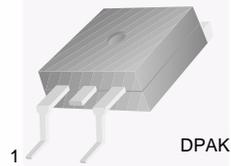


April 2012

FJD3305H1 NPN Silicon Transistor

Features

- High Voltage Switch Mode Application
- Fast Speed Switching
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application
- Wave Soldering



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	4	A
I_{CP}	Collector Current (Pulse)	8	A
I_B	Base Current	2	A
P_C	Collector Dissipation, $T_a = 25^\circ\text{C}$ $T_C = 25^\circ\text{C}$	1.1	W
		50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 to 150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	110	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.0	$^\circ\text{C}/\text{W}$

* Device mounted on minimum pad size

Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
FJD3305H1TM	J3305H1	D-PAK	Tape & Reel	

Electrical Characteristics* $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 500\mu\text{A}, I_E = 0$	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500\mu\text{A}, I_C = 0$	9			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 700\text{V}, I_E = 0$			1	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			1	μA
h_{FE1} h_{FE2}	DC Current Gain *	$V_{CE} = 5\text{V}, I_C = 1\text{A}$ $V_{CE} = 5\text{V}, I_C = 2\text{A}$	19 8		28 40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2\text{A}, I_B = 0.5\text{A}$ $I_C = 4\text{A}, I_B = 1\text{A}$			0.5 0.6 1.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2\text{A}, I_B = 0.5\text{A}$			1.2 1.6	V V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	4			MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		65		pF
t_{ON}	Turn On Time	$V_{CC} = 125\text{V}, I_C = 2\text{A}$			0.8	μs
t_{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.4\text{A}$			4.0	μs
t_F	Fall Time	$R_L = 62.5\Omega$			0.9	μs

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

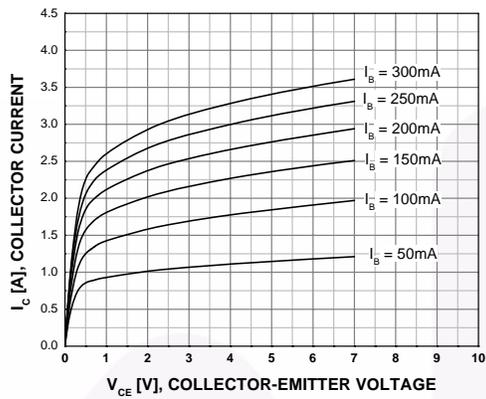


Figure 1. Static Characteristic

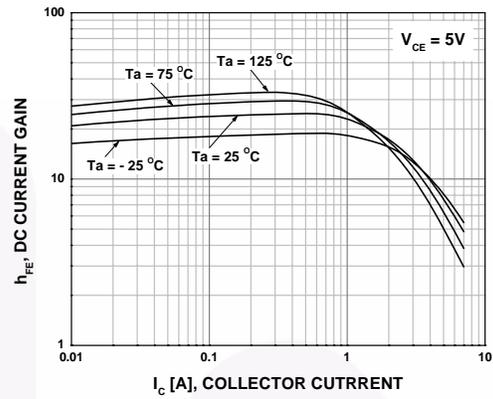


Figure 2. DC Current Gain

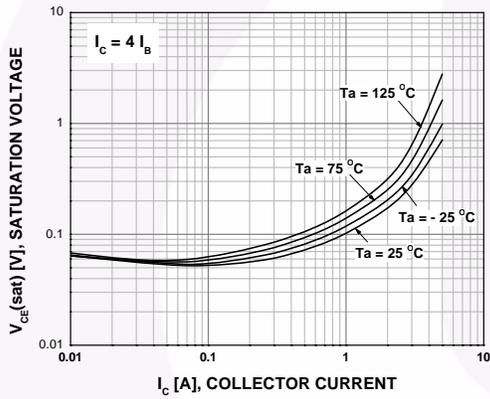


Figure 3. Collector- Emitter Saturation Voltage

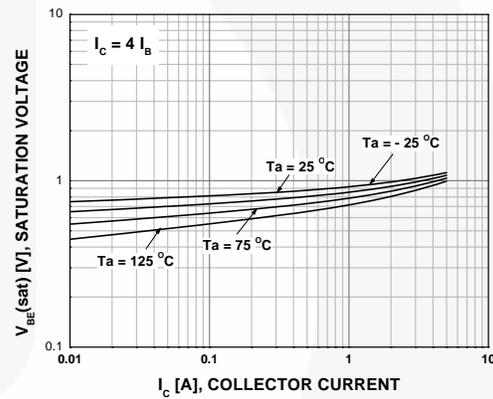


Figure 4. Base - Emitter Saturation Voltage

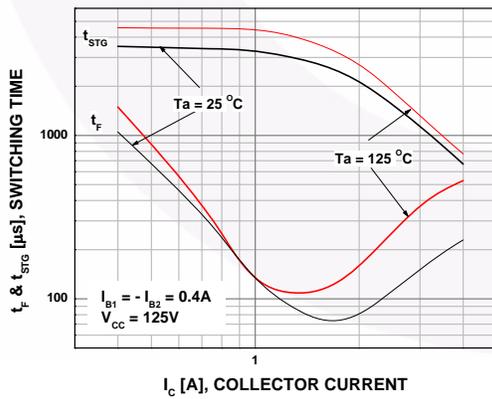


Figure 5. Switching Time

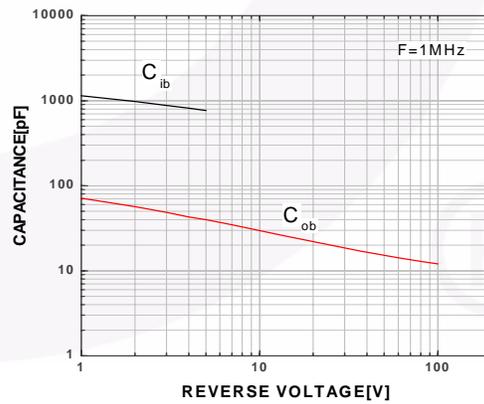


Figure 6. Capacitance

Typical Performance Characteristics (Continued)

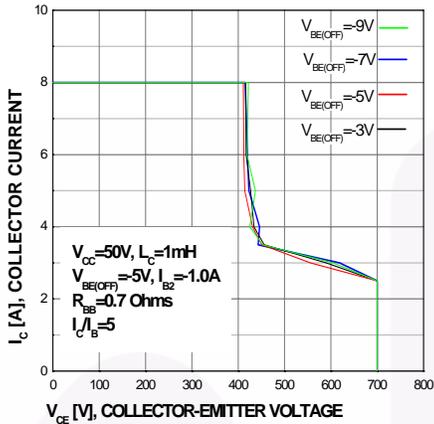


Figure 7. Reverse Biased Safe Operating Area

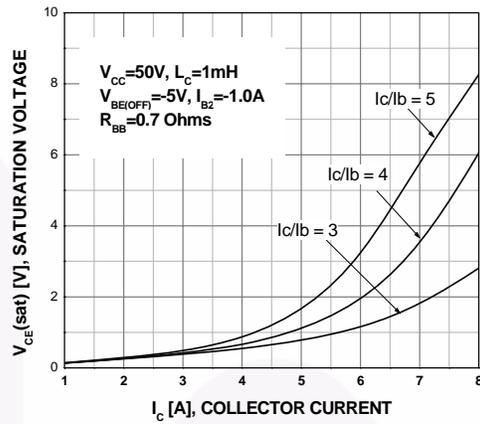


Figure 8. Collector- Emitter Saturation Voltage at RBSOA

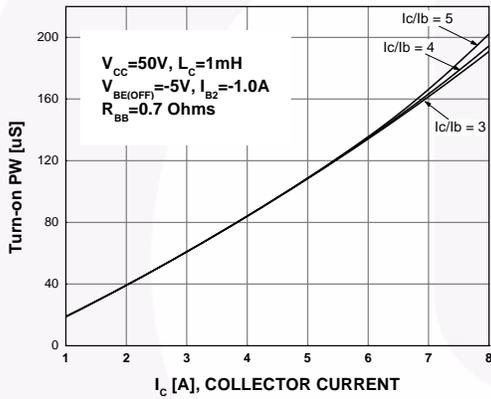


Figure 9. Input Pulse width vs Correct current at RBSOA

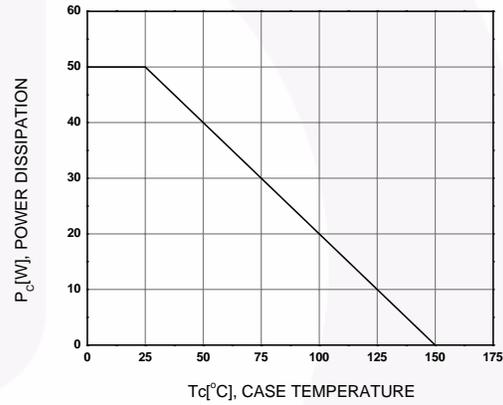


Figure 10. Power Derating

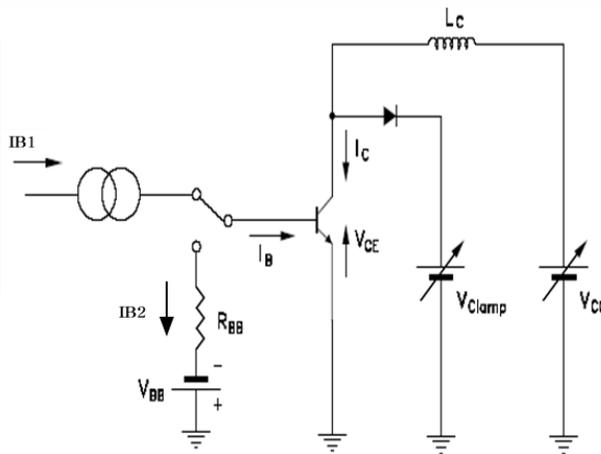
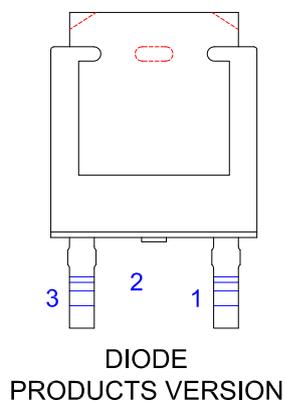
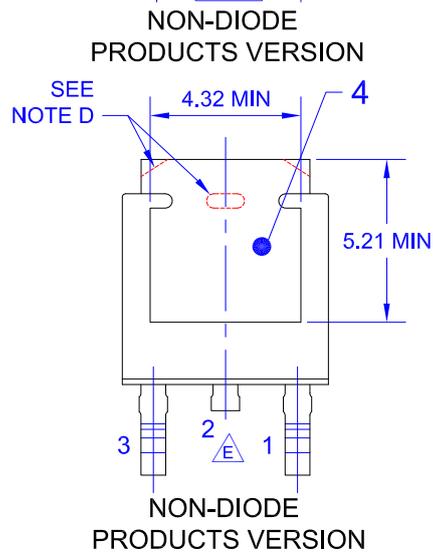
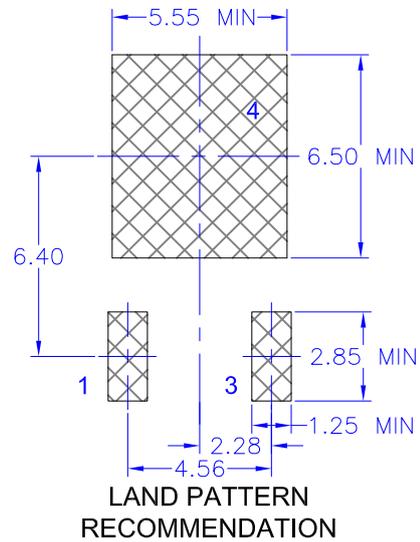
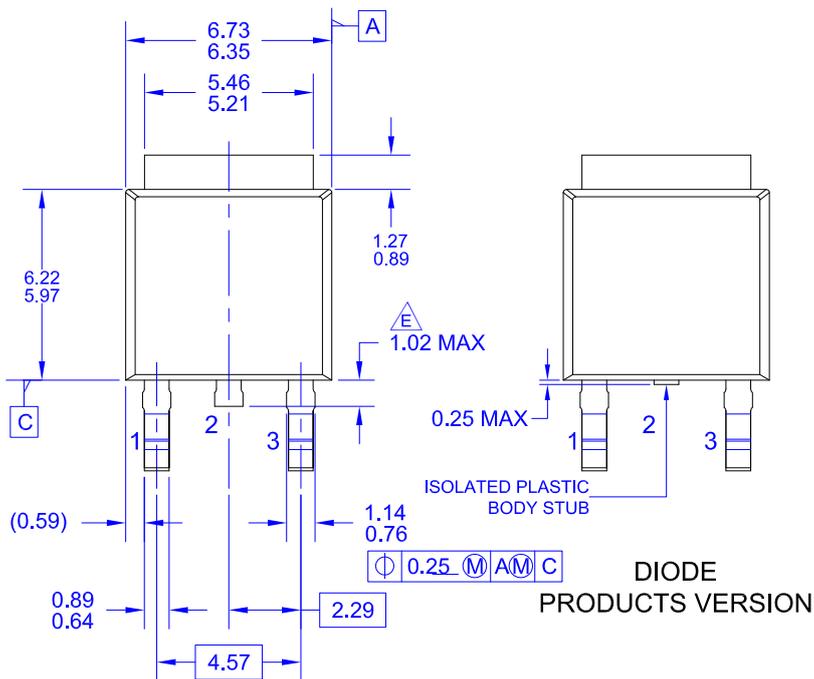


Figure 11. RBSOA Test Circuit



NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

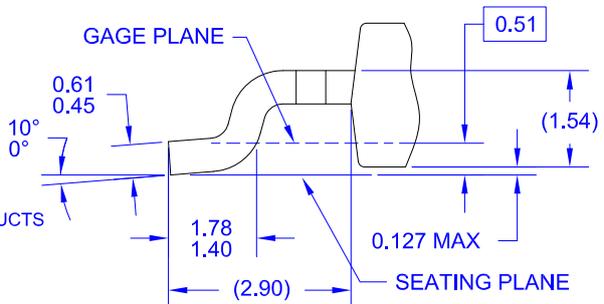
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



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